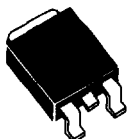


CJD31C NPN
CJD32C PNP

COMPLEMENTARY SILICON
POWER TRANSISTOR

DKAK
POWER!



DKAK CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CJD31C, CJD32C types are Complementary Silicon Power Transistors manufactured by the epitaxial base process, mounted in a surface mount package designed for power amplifier and high speed switching applications.

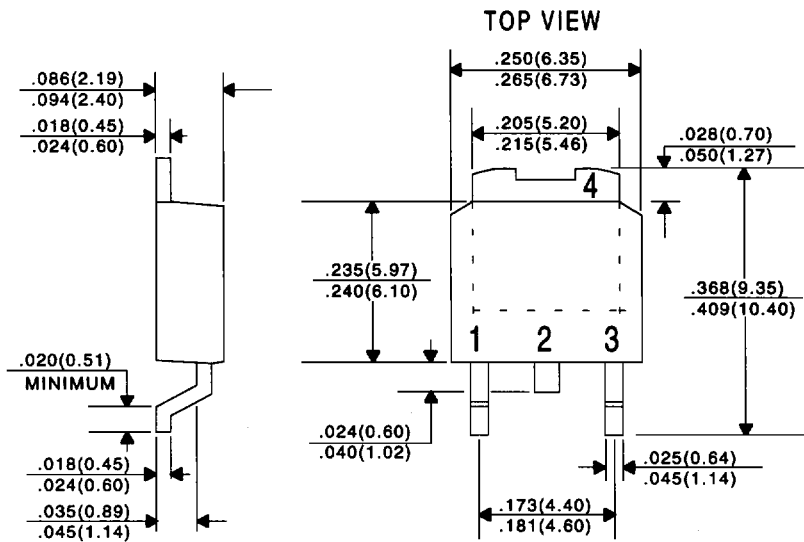
MAXIMUM RATINGS (T_C=25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V _{CBO}	100	V
Collector-Emitter Voltage	V _{CEO}	100	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Continuous Collector Current	I _C	3.0	A
Peak Collector Current	I _{CM}	5.0	A
Base Current	I _B	1.0	A
Power Dissipation (T _C =25°C)	P _D	15	W
Power Dissipation (T _A =25°C)	P _D	1.56	W
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JC}	8.33	°C/W
Thermal Resistance	θ _{JA}	80.1	°C/W

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{CEO}	V _{CE} =60V		50	μA
I _{CES}	V _{CE} =100V		20	μA
I _{EBO}	V _{EB} =5.0V		1.0	mA
BV _{CEO}	I _C =30mA	100		V
V _{CE(SAT)}	I _C =3.0A, I _B =375mA		1.2	V
V _{BE(ON)}	V _{CE} =4.0V, I _C =3.0A		1.8	V
h _{FE}	V _{CE} =4.0V, I _C =1.0A	25		
h _{FE}	V _{CE} =4.0V, I _C =3.0A	10	50	
f _T	V _{CE} =10V, I _C =500mA, f=1.0MHz	3.0		MHz
h _{fe}	V _{CE} =10V, I _C =500mA, f=1.0kHz	20		

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR

DATA
SHEET

R2